

IEEE EDS Fellows Elected 2023

Since 1963, IEEE has acknowledged those individuals who have contributed to the advancement of engineering science and technology. The honor of Fellow is bestowed on the recipient who has had an extraordinary record of accomplishments in any of the IEEE fields of interest. To learn more about the IEEE Fellow Program: <https://www.ieee.org/membership/fellows/index.html>.

Congratulations to the 21 EDS members elected to IEEE Grade of Fellow in 2023.



Shekhar Bhansali - for contributions to portable realtime sensing devices for continuous monitoring



Kyung Cheol CHOI - for contributions to emissive, flexible, and wearable displays



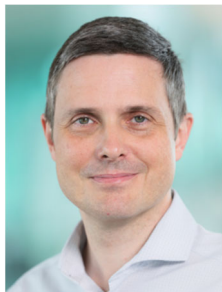
Tetsuo Endoh - for contributions to nonvolatile memory and spintronic logic



Harald Gossner - for contributions to ESD design of advanced IC devices and high speed systems



Masataka Higashiwaki- for contributions to gallium oxide electronics and millimeter-wave gallium nitride transistors



Andras Kis - for contributions to the development of 2D materials and electronic devices



Guann-pyng Li - for contributions to the bipolar device, circuit and technology in silicon and compound semiconductors



Takashi Matsuoka - for contributions to laser diodes for optical communications and nitride semiconductors for light emitting devices



Thomas Mikolajick - for contributions to nonvolatile memory



Yoshiaki Nakano - for contributions to semiconductor integrated photonic devices and circuits



Kenichi Okada - for contributions to millimeter-wave communication circuits design



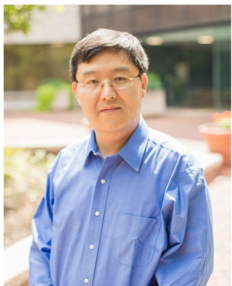
Boon S. Ooi - for contributions to broadband light emitters and visible light communications



Guann Pyng Li - for contributions to the bipolar device, circuit and technology in silicon and compound semiconductors



Munaf T Rahimo - for contributions to high-voltage insulated gate bipolar transistors for grid applications



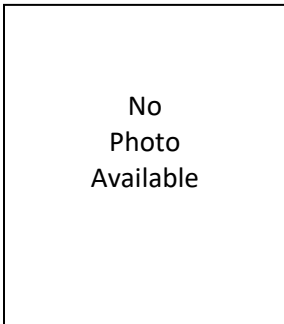
Sei-Hyung Ryu - for contributions to silicon carbide power device technology



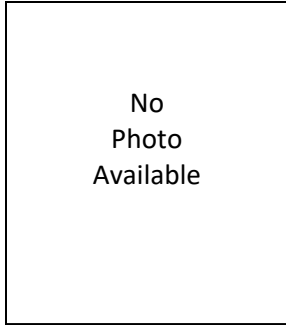
Abu Sebastian - for contributions to in-memory computing for scientific applications



Dmitri Strukov - for contributions to neuromorphic and alternative computing systems based on emerging memory devices



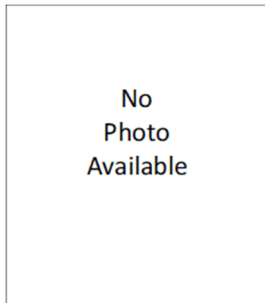
Richard Syms - for contributions to mass spectrometers based on microelectromechanical system technology



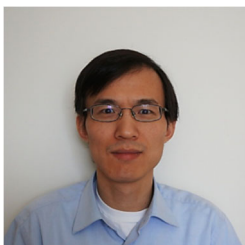
Miguel Urteaga – for contributions to terahertz heterojunction bipolar transistor integrated circuit technology



Pierre Verlinden - for leadership in high performance silicon solar cell and photovoltaics technology and commercialization



Hua Wang - for contributions to high-efficiency microwave and millimeter-wave power amplifiers



Qiangfei Xia - for contributions to resistive memory arrays and devices for in-memory computing